



YOUSHANG SEMICONDUCTOR

**设计研发新型功率器件**

**各类小信号开关**

**中低压及高压大电流等场效应管**

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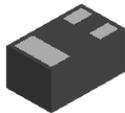
## Features

- $BV_{CEO} > -45V$
- $I_C = -100mA$  High Collector Current
- $P_D = 1000mW$  Power Dissipation
- $0.60mm^2$  Package Footprint, 13 Times Smaller Than SOT23
- 0.5mm Height Package Minimizing Off-Board Profile
- Complementary NPN Type: NK-BC847BLP

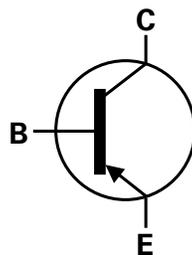
## Mechanical Data

- Package: X1-DFN1006-3
- Package Material: Molded Plastic, "Green" Molding Compound.  
UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish — NiPdAu, Solderable per MIL-STD-202,  
Method 208 [e4](#)
- Weight: 0.0009 grams (Approximate)

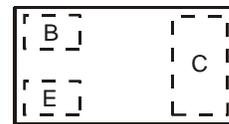
X1-DFN1006-3



Bottom View



Device Symbol



Top View  
Pinout

**Absolute Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	-50	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-45	V
Emitter-Base Voltage	V <sub>EBO</sub>	-5.0	V
Collector Current	I <sub>C</sub>	-100	mA
Peak Pulse Collector Current	I <sub>CM</sub>	-200	mA

**Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation	P <sub>D</sub>	(Note 5) 400	mW
		(Note 6) 1000	
Thermal Resistance, Junction to Ambient	R <sub>θJA</sub>	(Note 5) 310	°C/W
		(Note 6) 120	
Thermal Resistance, Junction to Lead	R <sub>θJL</sub>	120	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

- Notes:
5. For the device mounted on minimum recommended pad layout 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in steady state condition. The entire exposed collector pad is attached to the heatsink.
  6. Same as Note 5, except the exposed collector pad is mounted on 25mm x 25mm 2oz copper.
  7. Thermal resistance from junction to solder-point (on the exposed collector pad).

**ESD Ratings** (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	200	V	B

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	-50	—	—	V	I <sub>C</sub> = 100μA
Collector-Emitter Breakdown Voltage (Note 9)	BV <sub>CEO</sub>	-45	—	—	V	I <sub>C</sub> = 10mA
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	-5	—	—	V	I <sub>E</sub> = 100μA
DC Current Gain	h <sub>FE</sub>	220	260	475	—	V <sub>CE</sub> = -5.0V, I <sub>C</sub> = -2.0mA
Collector-Emitter Saturation Voltage (Note 9)	V <sub>CE(sat)</sub>	—	-90 -250	-300 -650	mV	I <sub>C</sub> = -10mA, I <sub>B</sub> = -0.5mA I <sub>C</sub> = -100mA, I <sub>B</sub> = -5.0mA
Base-Emitter Saturation Voltage (Note 9)	V <sub>BE(sat)</sub>	—	-700 -850	—	mV	I <sub>C</sub> = -10mA, I <sub>B</sub> = -0.5mA I <sub>C</sub> = -100mA, I <sub>B</sub> = -5.0mA
Base-Emitter Voltage (Note 9)	V <sub>BE(on)</sub>	-600 —	-670 -710	-750 -820	mV	V <sub>CE</sub> = -5.0V, I <sub>C</sub> = -2.0mA V <sub>CE</sub> = -5.0V, I <sub>C</sub> = -10mA
Collector-Cutoff Current	I <sub>CBO</sub>	— —	— —	-15 -4.0	nA μA	V <sub>CB</sub> = -30V V <sub>CB</sub> = -30V, T <sub>A</sub> = +150°C
Gain Bandwidth Product	f <sub>T</sub>	100	—	—	MHz	V <sub>CE</sub> = -5.0V, I <sub>C</sub> = -10mA, f = 100MHz
Collector-Base Capacitance	C <sub>CBO</sub>	—	3.0	—	pF	V <sub>CB</sub> = -10V, f = 1.0MHz

Notes: 8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.  
 9. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%.

**Typical Electrical Characteristics** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

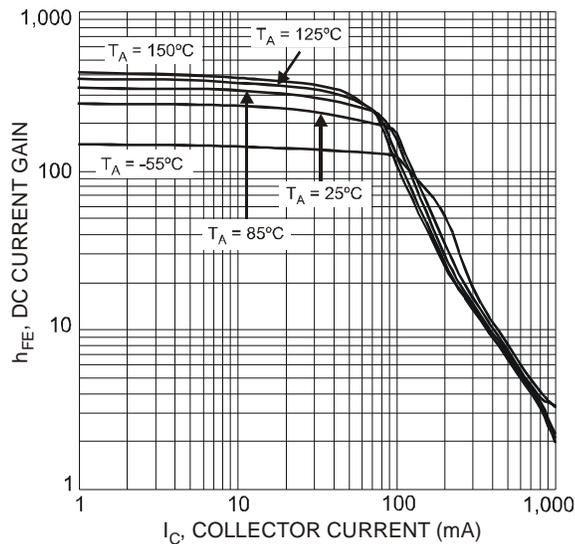


Fig. 1 Typical DC Current Gain vs. Collector Current

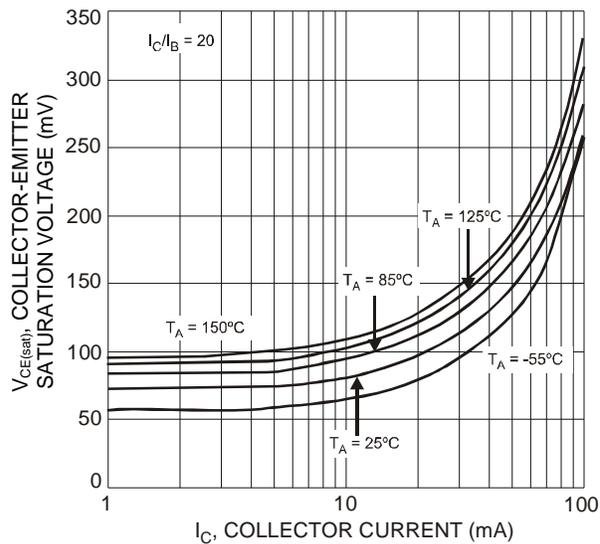


Fig. 2 Typical Collector-Emitter Saturation Voltage vs. Collector Current

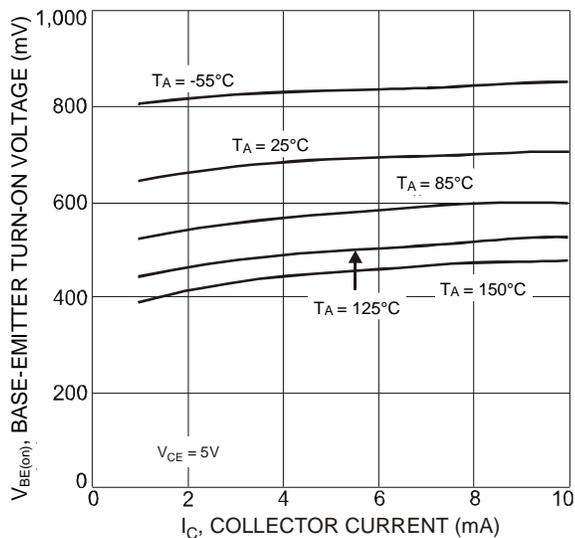


Fig. 3 Typical Base-Emitter Turn-On Voltage vs. Collector Current

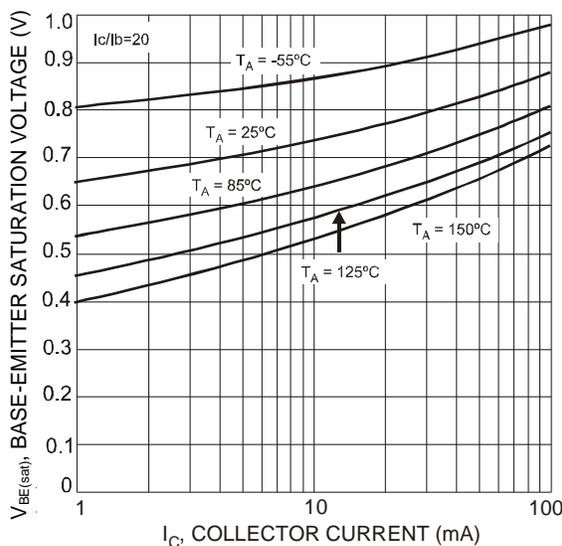
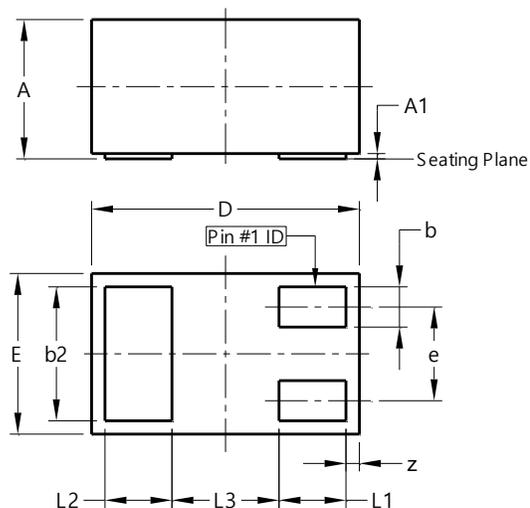


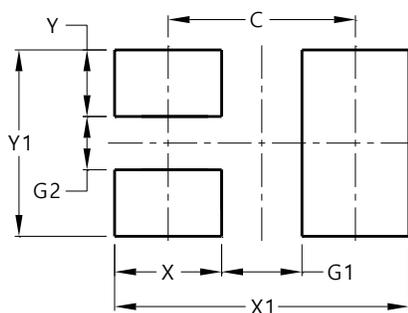
Fig. 4 Typical Base-Emitter Saturation Voltage vs. Collector Current

## Package Outline Dimensions

**X1-DFN1006-3**


X1-DFN1006-3			
Dim	Min	Max	Typ
A	0.47	0.53	0.50
A1	0.00	0.05	0.03
b	0.10	0.20	0.15
b2	0.45	0.55	0.50
D	0.95	1.075	1.00
E	0.55	0.675	0.60
e	-	-	0.35
L1	0.20	0.30	0.25
L2	0.20	0.30	0.25
L3	-	-	0.40
z	0.02	0.08	0.05
All Dimensions in mm			

## Suggested Pad Layout

**X1-DFN1006-3**


Dimensions	Value (in mm)
C	0.70
G1	0.30
G2	0.20
X	0.40
X1	1.10
Y	0.25
Y1	0.70